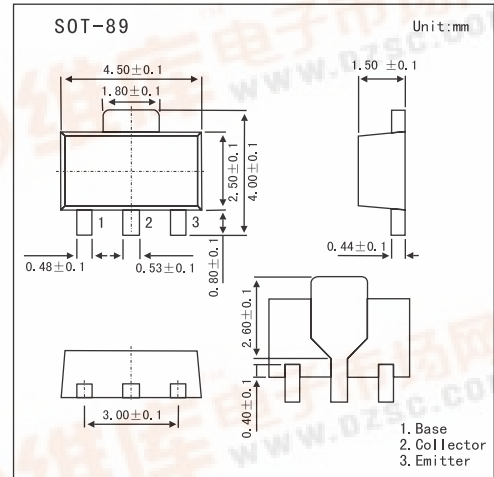


SMD Type Transistors

Silicon PNP Epitaxial  
2SA1944

Features

- High voltage  $V_{CE0}=-50V$
- Low collector to emitter saturation voltage  
 $V_{CE(sat)}=-0.2v$  typ (@ $I_c=-500mA, I_B=-10mA$ )
- High  $h_{FE}$ :  $h_{FE}=400$  to  $800$
- Small package for mounting



Absolute Maximum Ratings  $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Peak collector current	$I_{CM}$	-2	A
Collector current	$I_c$	-1	A
Collector dissipation ( $T_a=25^\circ C$ )	$P_C$	500	mW
Jumction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-10\mu A, I_E=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_c=0$	-6			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-1mA, R_{BE}=\infty$	-50			V
Collector cutoff current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-0.1	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=-2V, I_c=0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-6V, I_c=-100mA$	400		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=-500mA, I_B=-10mA$		-0.2	-0.5	V
Gain bandwidth product	$f_T$	$V_{CE}=-10V, I_E=-10mA$		90		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		30		pF

Marking

Marking	XG
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